IN THE CLAIMS

Listing of Claims:

1 – 17. (Cancelled)

18. (New) A method, comprising:

forming a first layer over a substrate, the first layer sensitive to a first chemistry;

forming a second layer on the first layer, the second layer formed to a first thickness and the second layer not sensitive to the first chemistry;

forming a third layer over the second layer, the third layer removable by the first chemistry;

patterning the third layer to have an opening;

etching a substantial thickness of the second layer through the opening, leaving a thin, unetched portion of the second layer on the first layer, the thin unetched portion having a second thickness;

removing the third layer using the first chemistry, the thin, unetched portion of the second layer protecting the first layer from the first chemistry;

removing the thin, unetched portion of the second layer using a second chemistry to which the first layer is not sensitive to provide an exposed first layer; and

conditioning a surface of the exposed first layer with a third chemistry after removing the thin, unetched portion of the second layer, the conditioning to terminate the surface of the exposed first layer with primarily the same atomic termini.

19. (New) The method of claim 18, wherein conditioning the surface of the exposed first layer comprises applying a conditioning chemistry to terminate the surface of the exposed first layer with hydride termini.

20. (New) The method of claim 19, further comprising depositing a conductive material on the exposed first layer.

21. (New) The method of claim 18, wherein conditioning the surface of the exposed first layer comprises applying a conditioning chemistry to terminate the surface of the exposed first layer with hydroxal termini.

22. (New) The method of claim 21, further comprising depositing a high-k dielectric material by atomic layer deposition on the exposed first layer.

23. (New) The method of claim 18, wherein forming the first layer over the substrate comprises forming a layer of any one of germanium, gallium arsenide, aluminum nitride, or indium intiminide over the substrate.

24. (New) The method of claim 18, wherein the second thickness is approximately 10% to 25% of the first thickness.

25. (New) The method of claim 18, wherein the first layer is a germanium material, the second layer is a nitride, and the third layer is a photoresist material.

26. (New) The method of claim 18, wherein removing a substantial portion of the second layer includes performing a timed dry etch to the second layer through the opening, the timed etch timed to remove approximately 75% - 90% of the second layer.